
Semiconductors, Dielectrics, and Metals for Nanoelectronics 12

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Sponsoring Divisions:



Dielectric Science & Technology



Electronics and Photonics



Published by

The Electrochemical Society

65 South Main Street, Building D
Pennington, NJ 08534-2839, USA

tel 609 737 1902

fax 609 737 2743

www.electrochem.org

ecsttransactions™

Vol. 64, No. 8

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Published by:

The Electrochemical Society
65 South Main Street
Pennington, New Jersey 08534-2839, USA

Telephone 609.737.1902
Fax 609.737.2743
e-mail: ecs@electrochem.org
Web: www.electrochem.org

ISSN 1938-6737 (online)
ISSN 1938-5862 (print)
ISSN 2151-2051 (cd-rom)

ISBN 978-1-62332-188-8 (Hard Cover)
ISBN 978-1-60768-545-6 (PDF)

Printed in the United States of America.

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